

March 2015

600 V, 40 A Field Stop IGBT

Features

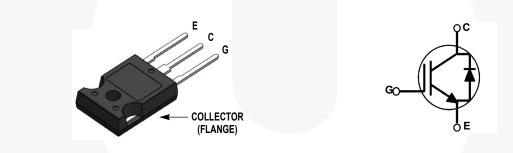
- · High Current Capability
- Low Saturation Voltage: V_{CE(sat)} = 1.8 V @ I_C = 40 A
- High Input Impedance
- · Fast Switching
- RoHS Compliant

Applications

· Solar Inverter, UPS, Welder, PFC, Microwave Oven, Telecom, ESS

General Description

Using novel field stop IGBT technology, Fairchild's field stop IGBTs offer the optimum performance for solar inverter, UPS, welder, microwave oven, telecom, ESS and PFC applications where low conduction and switching losses are essential.



Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
V _{CES}	Collector to Emitter Voltage		600	V
V _{GES}	Gate to Emitter Voltage	± 20	V	
	Transient Gate-to-Emitter Voltage		± 30	V
Ι _C	Collector Current	@ T _C = 25°C	80	А
	Collector Current	@ T _C = 100 ^o C	40	А
I _{CM (1)}	Pulsed Collector Current	@ T _C = 25°C	120	А
P _D	Maximum Power Dissipation	@ T _C = 25°C	290	W
	Maximum Power Dissipation	@ T _C = 100 ^o C	116	W
TJ	Operating Junction Temperature	-55 to +150	°C	
T _{stg}	Storage Temperature Range		-55 to +150	°C
Τ _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	°C	

Notes: 1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
R _{0JC} (IGBT)	Thermal Resistance, Junction to Case	-	0.43	°C/W
$R_{\theta JC}$ (Diode)	Thermal Resistance, Junction to Case	-	1.45	°C/W
R _{θJA}	R _{0JA} Thermal Resistance, Junction to Ambient		40	°C/W

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Part Nu	mber	Top Mark	Package	Packing Method	Reel Size	Tape Wio	dth 🤇	Quantity
FGH40N60UFDTU FGH40N60UFD TO-247		TO-247	Tube	N/A	N/A		30	
Electrica	al Cha	aracteristics	of the IG	BT T _C = 25°C unless other	wise noted			
Symbol		Parameter		Test Condition	ns Min.	Тур.	Max.	Unit
Off Charact	teristics							
BV _{CES}	Collecto	r to Emitter Breakdo	own Voltage	V _{GE} = 0 V, I _C = 250 μA	600	_	-	V
$\frac{\Delta BV_{CES}}{\Delta T_{J}}$	Collector to Emitter Breakdown Voltage Temperature Coefficient of Breakdown Voltage		Proakdown	V _{GE} = 0 V, I _C = 250 μA	-	0.6	-	V/ºC
I _{CES}	Collecto	r Cut-Off Current		V _{CE} = V _{CES} , V _{GE} = 0 V	-	-	250	μA
I _{GES}	G-E Lea	kage Current		$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±400	nA
					I			
On Charact								
V _{GE(th)}	G-E Thr	eshold Voltage		$I_C = 250 \ \mu A, \ V_{CE} = V_{GE}$	4.0	5.0	6.5	V
Varia	Collecto	to Emitter Saturation Voltage		I _C = 40 A, V _{GE} = 15 V	-	1.8	2.4	V
V _{CE(sat)}	t) Collector to Emitter Saturation Voltage			I _C = 40 A, V _{GE} = 15 V, T _C = 125 ^o C	-	2.0	-	V
Dynamic C	haracter	istics						
C _{ies}	Input Capacitance				-	2110	-	pF
C _{oes}	Output (Capacitance		V _{CE} = 30 V _, V _{GE} = 0 V, f = 1 MHz	-	200	-	pF
C _{res}	Reverse Transfer Capacitance				-	60	-	pF
Switching (Characte	ristics						
t _{d(on)}	Turn-On Delay Time				-	24	-	ns
t _r	Rise Tin	Rise Time Turn-Off Delay Time all Time Turn-On Switching Loss Turn-Off Switching Loss			-	44	-	ns
t _{d(off)}	Turn-Of			V _{CC} = 400 V, I _C = 40 A,	-	112	-	ns
t _f	Fall Tim			$R_{G} = 10 \Omega, V_{GE} = 15 V,$	-	30	60	ns
E _{on}	Turn-Or			Inductive Load, $T_C = 25^{\circ}$	C -	1.19	-	mJ
E _{off}	Turn-Of				-	0.46	- 1	mJ
E _{ts}	Total Sv	vitching Loss			-	1.65	-	mJ
t _{d(on)}	Turn-Or	urn-On Delay Time ise Time urn-Off Delay Time all Time urn-On Switching Loss urn-Off Switching Loss			-	24	-	ns
t _r	Rise Tin				-	45	-	ns
t _{d(off)}	Turn-Of			V _{CC} = 400 V, I _C = 40 A,	-	120	-	ns
t _f	Fall Tim			$R_{G} = 10 \Omega, V_{GE} = 15 V,$		40	-	ns
E _{on}	Turn-Or			Inductive Load, $T_C = 125$	-	1.2	-	mJ
E _{off}	Turn-Of				-	0.69	-	mJ
E _{ts}	Total Sv	vitching Loss			-	1.89	-	mJ
Qg	Total Ga	ate Charge			-	120	-	nC
Q _{ge}	Gate to	Emitter Charge		V _{CE} = 400 V, I _C = 40 A, V _{GE} = 15 V	-	14	-	nC
Q _{gc}	Gate to	ate to Collector Charge		GE - IO V	_	58	-	nC

5	Min.	Тур.	Max	Unit	
Г _С = 25 ^о С	-	1.95	2.6	v	
Г _С = 125 ^о С	-	1.85	-		
Г _С = 25 ^о С	-	45	-	ns	
Г _С = 125°С	-	140	-		
Г _С = 25 ^о С	-	75	-	nC	
Г _С = 125 ^о С	-	375	-		

Electrical Characteristics of the Diode T_C = 25°C unless otherwise noted

I_F = 20 A

Parameter

Diode Reverse Recovery Time

Diode Reverse Recovery Charge

Diode Forward Voltage

Test Conditions

 $I_{\rm F}$ =20 A, di_F/dt = 200 A/µs

Symbol

 V_{FM}

t_{rr}

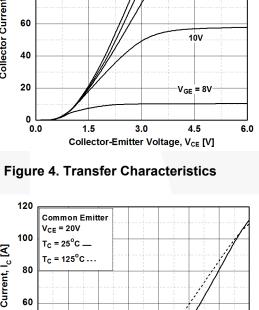
Q_{rr}

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Typical Performance Characteristics Figure 1. Typical Output Characteristics 120 120 T_C = 125°C T_C = 25°C 15V 12V 20V 20V 100 100 Collector Current, Ic [A] Collector Current, I_c [A] 80 80 60 60 10V 40 40 20 20 $V_{GE} = 8V$ 0 0 0.0 4.5 0.0 1.5 1.5 3.0 6.0 Collector-Emitter Voltage, V_{CE} [V] **Figure 3. Typical Saturation Voltage** Characteristics 120 120 Common Emitter Common Emitter V_{CE} = 20V V_{GE} = 15V 100 100 T_C = 25^oC ___ T_C = 25°C ____ Collector Current, I_c [A] Collector Current, Ic [A] = 125[°]C ... T_C = 125[°]C Тc 80 80 60 60 40 40 20 20 0 0 3 0 2 5 6 8 1 7 Collector-Emitter Voltage, V_{CE} [V] Figure 5. Saturation Voltage vs. Case **Temperature at Variant Current Level** 3.5 Common Emitter 20 V_{GE} = 15V Collector-Emitter Voltage, V_{CE} [V] 9.1 0.7 5.7 0.6 [V] Collector-Emitter Voltage, V_{CE} [V] 80A 16 12 40A 8 I_C = 20A I_C = 20A 1.0 ٥ ^ل 25 50 75 100 125 8 Case Temperature, T_c [°C]

Figure 2. Typical Output Characteristics

15V



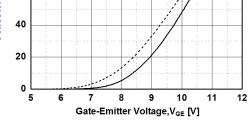
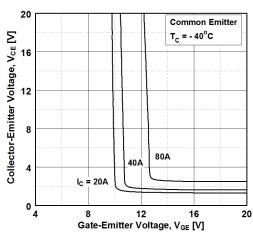


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics



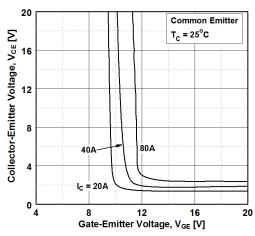
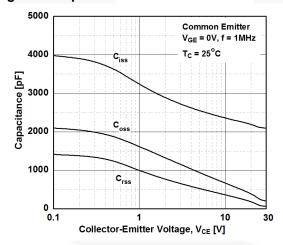


Figure 9. Capacitance Characteristics





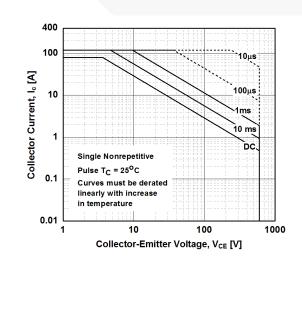


Figure 8. Saturation Voltage vs. VGE

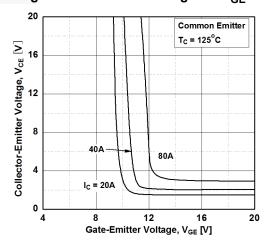


Figure 10. Gate charge Characteristics

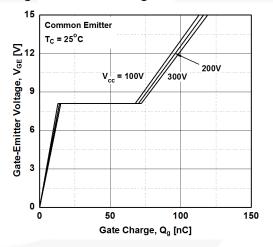
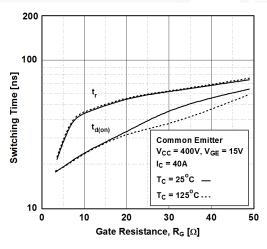
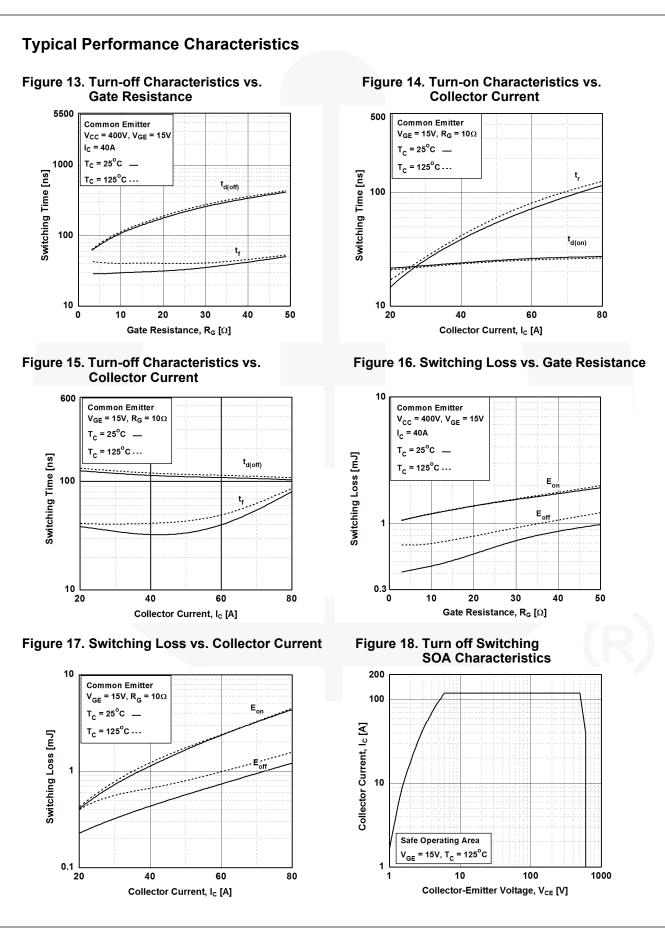
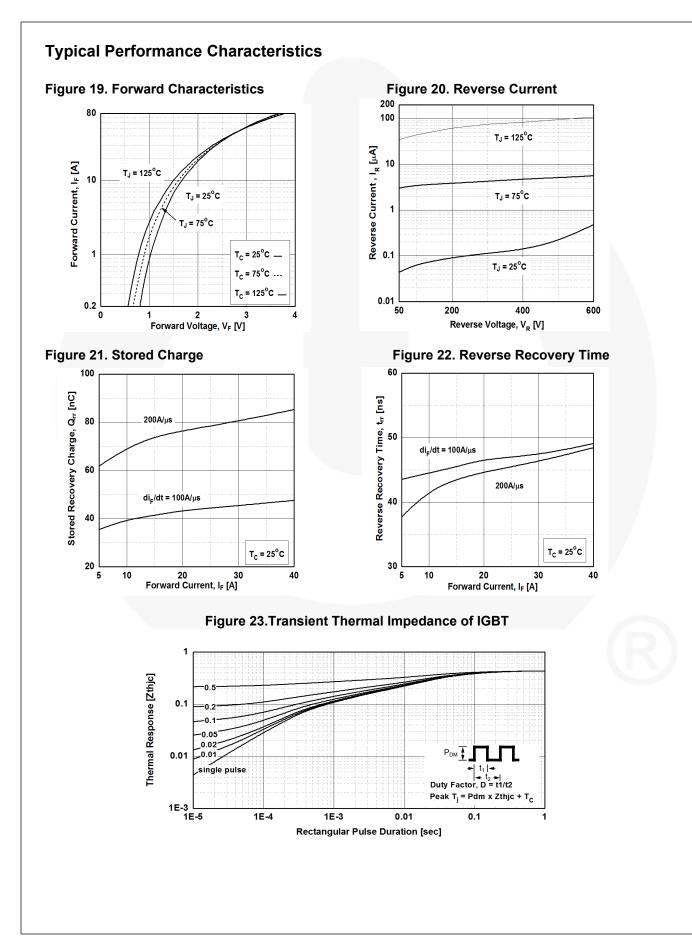
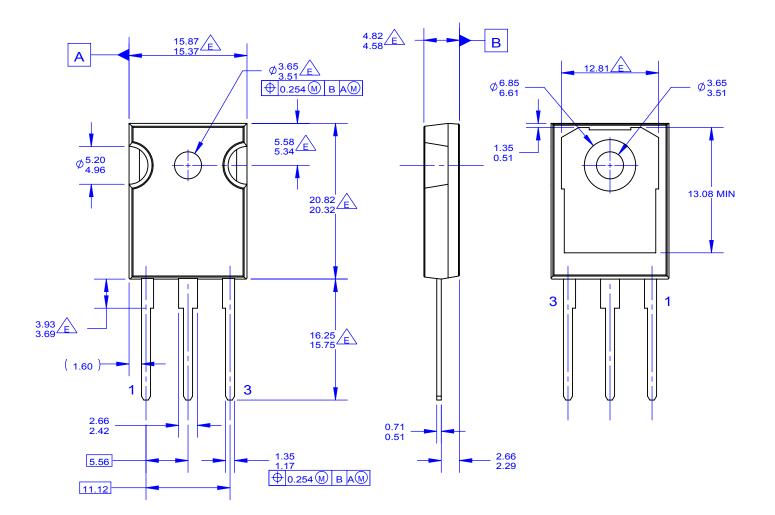


Figure 12. Turn-on Characteristics vs. Gate Resistance









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